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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100llafa-v0

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Table 1-1. List of Ordering Part Numbers

Dia	Destaurs	Data flash		(3/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CCALA#W0, R5F100CDALA#W0, R5F100CEALA#W0, R5F100CFALA#W0, R5F100CGALA#W0
			G	R5F100CAGLA#U0, R5F100CCGLA#U0, R5F100CDGLA#U0, R5F100CEGLA#U0, R5F100CFGLA#U0, R5F100CGGLA#U0 R5F100CAGLA#W0, R5F100CCGLA#W0, R5F100CDGLA#W0, R5F100CEGLA#W0, R5F100CFGLA#W0, R5F100CGGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0, R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0, R5F100EHANA#W0
			D	R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0
			G	R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EGGNA#W0, R5F100EHGNA#W0
		Not mounted	A	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EFANA#W0, R5F101EGANA#W0, R5F101EHANA#W0
			D	R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EFDNA#U0, R5F101EGDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EEDNA#W0, R5F101EFDNA#W0, R5F101EGDNA#W0, R5F101EHDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.14 128-pin products

• 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

- 2. Make VDD pin the potential that is higher than EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

							(1/2)				
	Item	80-	•	100)-pin	128-pin					
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx				
Code flash m	emory (KB)	96 te	o 512	96 to 512		192 to 512					
Data flash me	emory (KB)	8	_	8	-	8	-				
RAM (KB)		8 to 3	2 Note 1	8 to 3	32 Note 1	16 to 5	32 Note 1				
Address space	e	1 MB									
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	mic) oscillation, I main) mode: 1 I main) mode: 1 main) mode: 1 e main) mode: 1	to 20 MHz (V_{DD} to 16 MHz (V_{DD} to 8 MHz (V_{DD} =	= 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)					
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	I main) mode: 1 I main) mode: 1 main) mode: 1 e main) mode: 1	to 16 MHz (V _{DD} to 8 MHz (V _{DD} =	= 2.4 to 5.5 V), 1.8 to 5.5 V),						
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	I subsystem cloc	k input (EXCLKS	i)					
Low-speed or	n-chip oscillator	15 kHz (TYP.)									
General-purp	ose register	(8-bit register × 8) × 4 banks									
Minimum inst	ruction execution time	0.03125 μ s (High-speed on-chip oscillator: fi H = 32 MHz operation)									
		0.05 μ s (High-speed system clock: f _{MX} = 20 MHz operation)									
		30.5 µs (Subsystem clock: fsub = 32.768 kHz operation)									
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 									
I/O port	Total	7	74	92		120					
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand le]: 21)	(N-ch O.D. I/O	82 [EV⊳⊳ withstand ge]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand ge]: 25)				
	CMOS input		5		5		5				
	CMOS output		1		1		1				
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4				
Timer	16-bit timer	12 cha	annels	12 ch	annels	16 ch	annels				
	Watchdog timer	1 cha	annel	1 ch	annel	1 cha	annel				
	Real-time clock (RTC)	1 cha	annel	1 ch	annel	1 cha	annel				
	12-bit interval timer (IT)	1 cha	annel	1 ch	annel	1 cha	annel				
	Timer output	12 channels (PWM outputs:	10 ^{Note 2})	12 channels (PWM outputs:	10 Note 2)	16 channels (PWM outputs:	14 Note 2)				
	RTC output	1 channel • 1 Hz (subsyster)	tem clock: fsub =	32.768 kHz)							

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library** for RL78 Family (R20UT2944).



2.3 DC Characteristics

2.3.1 Pin characteristics

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$1.6~V \leq EV_{DD0} \leq 5.5~V$			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-55.0	mA
		P125 to P127, P130, P140 to P145	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
			$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
			$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,				-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
		P117, P146, P147	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			-10.0	mA
		(When duty \leq 70% ^{Note 3})	$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			-5.0	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$			-135.0 Note 4	mA
	Іон2	Per pin for P20 to P27, P150 to P156	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

- 2. However, do not exceed the total current value.
- **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- **4.** The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is -100 mA.
- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	Iol1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty $\leq 70\%^{Note 3}$) Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67,	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			70.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			15.0	mA
			$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			9.0	mA
			$1.6~V \leq EV_{\text{DD0}} < 1.8~V$			4.5	mA
			$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			80.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146,	$1.8~V \leq EV_{\text{DD0}} < 2.7~V$			20.0	mA
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$			10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)				150.0	mA
	Iol2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$1.6~V \leq V_{\text{DD}} \leq 5.5~V$			5.0	mA

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = EV_{SS0} = EV_{SS1} = 0 \text{ V})$ (2/5)

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(I_{OL} \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OL} = 10.0 \text{ mA}$

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditio	ons		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Цінт	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVDDO				1	μA
	Ілна	P20 to P27, P137, P150 to P156, RESET	$V_{\text{I}} = V_{\text{DD}}$				1	μA
	Іцнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	luu1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso				-1	μΑ
	Ilile	P20 to P27, P137, P150 to P156, RESET	VI = Vss				-1	μA
	Ililis	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso	, In input port	10	20	100	kΩ

$(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ (5/5)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter Symbol		o Conditions		HS (high-speed LS (low-spe main) Mode Mod			,	LV (low-voltage main) Mode		Unit					
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.						
SIp setup time (to SCKp↑) ^{Note 1}	tsik2	2.7 V ≤ E	$EV_{DD0} \leq 5.5 V$	1/fмск+2 0		1/fмск+30		1/fмск+30		ns					
		1.8 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+3 0		1/fмск+30		1/fмск+30		ns					
		1.7 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+4 0		1/fмск+40		1/fмск+40		ns					
		1.6 V ≤	$EV_{DD0} \leq 5.5 V$			1/fмск+40		1/fмск+40		ns					
SIp hold time (from SCKp↑)	tksı2	1.8 V ≤ E	$V_{DD0} \leq 5.5 \text{ V}$	1/fмск+3 1		1/fмск+31		1/fмск+31		ns					
Note 2		1.7 V ≤ E	$EV_{DD0} \leq 5.5 \text{ V}$	1/fмск+ 250		1/fмск+ 250		1/fмск+ 250		ns					
		1.6 V ≤	$EV_{DD0} \leq 5.5 V$	—		1/fмск+ 250		1/fмск+ 250		ns					
Delay time from SCKp↓ to	tkso2	C = 30 pF ^{Note 4}	$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/f _{мск+} 44		2/f _{мск+} 110		2/f _{мск+} 110	ns					
SOp output Note 3		V						$\begin{array}{l} 2.4 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 75		2/fмск+ 110		2/fмск+ 110	ns
			$\begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 110		2/fмск+ 110		2/fмск+ 110	ns					
			$\begin{array}{l} 1.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		2/fмск+ 220		2/fмск+ 220		2/fмск+ 220	ns					
			$\begin{array}{l} 1.6 \ V \leq EV_{\text{DD0}} \leq 5.5 \\ V \end{array}$		_		2/fмск+ 220		2/fмск+ 220	ns					

(4)	During communication at same potential (CSI mode) (slave mode, SCKp external clock input) (2/2)
	$(T_A = -40 \text{ to } \pm 85^{\circ}\text{C} = 1.6 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD1} \leq 5.5 \text{ V}_{D0} \text{ V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0.0 \text{ V}_{D1}$

- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)







Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode	``	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fsc∟	$\begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ p\text{F}, \ R_{\text{b}} = 2.7 \ k\Omega \end{array}$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$		400 Note 1		400 Note 1		400 Note 1	kHz
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_b = 100 \text{ pF}, \text{ R}_b = 5 \text{ k}\Omega$		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$		250 Note 1		250 Note 1		250 Note 1	kHz
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tlow	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	1150		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	1550		1550		1550		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, \text{R}_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 5 \text{ k}\Omega$			1850		1850		ns
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	1150		1150		1150		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V},$ $C_b = 100 \text{ pF}, \text{R}_b = 5 \text{ k}\Omega$	1550		1550		1550		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, \text{R}_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, \text{R}_b = 5 \text{ k}\Omega$			1850		1850		ns

(5) During communication at same potential (simplified I²C mode) (1/2)

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)



Parameter	Symbol		Conditions		speed	high- main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$\begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ 2.7 \ V \leq V_{b} \leq 4.0 \ V \end{array}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fмск/6 Note 1		fмск/6 Note 1		fмск/6 Note 1	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fмск = fclк ^{Note 4}		5.3		1.3		0.6	Mbps

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) (T_A = -40 to +85°C. 1.8 V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5 V. Vss = EV_{SS0} = EV_{SS1} = 0 V)

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4~V \leq EV_{\text{DD0}} < 2.7~V$: MAX. 2.6 Mbps

 $1.8~V \leq EV_{\text{DD0}} < 2.4~V$: MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

	16 MHz (2.4 V \leq VDD \leq 5.5 V)
LS (low-speed main) mode:	8 MHz (1.8 V \leq V_{DD} \leq 5.5 V)

LV (low-voltage main) mode: $4 \text{ MHz} (1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



3.3.2 Supply current characteristics

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-	$f_{IH}=32~MHz^{Note~3}$	Basic	$V_{DD} = 5.0 V$		2.1		mA
Current Note 1		mode	speed main) mode ^{Note 5}		operatio n	Vdd = 3.0 V		2.1		mA
					Normal	$V_{DD} = 5.0 V$		4.6	7.5	mA
					operatio n	$V_{DD} = 3.0 V$		4.6	7.5	mA
				$f_{IH} = 24 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 V$		3.7	5.8	mA
					operatio n	$V_{DD} = 3.0 V$		3.7	5.8	mA
				$f_{IH} = 16 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 V$		2.7	4.2	mA
					operatio n	V _{DD} = 3.0 V		2.7	4.2	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.0	4.9	mA
			speed main) mode ^{№ote 5}	$V_{DD} = 5.0 V$	operatio n	Resonator connection		3.2	5.0	mA
				$f_{MX} = 20 \text{ MHz}^{Note 2},$	Normal	Square wave input		3.0	4.9	mA
		$V_{DD} = 3.0 V$	operatio n	Resonator connection		3.2	5.0	mA		
				$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	mA
			$V_{DD} = 5.0 V$	operatio n	Resonator connection		1.9	2.9	mA	
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$ $V_{\text{DD}} = 3.0 \text{ V}$	$f_{MX} = 10 \text{ MHz}^{Note 2},$	Normal	Square wave input		1.9	2.9	mA
				operatio n	Resonator connection		1.9	2.9	mA	
			Subsystem	fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μA
		clock operation	Note 4 Ope $T_A = -40^{\circ}C$ n	operatio n	Resonator connection		4.2	5.0	μA	
				fsuв = 32.768 kHz	Normal	Square wave input		4.1	4.9	μA
			Note 4 $T_A = +25^{\circ}C$	operatio n	Resonator connection		4.2	5.0	μA	
				fsuв = 32.768 kHz	Normal	Square wave input		4.2	5.5	μA
				Note 4 $T_A = +50^{\circ}C$	operatio n	Resonator connection		4.3	5.6	μA
				fsuв = 32.768 kHz	Normal	Square wave input		4.3	6.3	μA
	Note 4	Note 4	operatio n	Resonator connection		4.4	6.4	μA		
				$T_A = +70^{\circ}C$	Newsel			4.0	~ ~	
	Note 4		fsub = 32.768 kHz Note 4	Normal operation	Square wave input		4.6	7.7	μA	
		T _A = +85°C	sportuoli	Resonator connection		4.7	7.8	μA		
				fsuв = 32.768 kHz	Normal	Square wave input		6.9	19.7	μA
				_{Note 4} T _A = +105°C	operation	Resonator connection		7.0	19.8	μA

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq EV_{DD0} \leq V_{DD} \leq 5.5$ V, Vss = EVss₀ = 0 V) (1/2)

(Notes and Remarks are listed on the next page.)



Parameter	Symbol	Conditions	Conditions HS (high-speed main) Mod		Unit
			MIN.	MAX.	
SIp setup time	tsik1	$4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_b \leq 4.0 \ V,$	162		ns
(to SCKp↑) ^{Note}		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \leq EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V,$	354		ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	958		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 5.5 \text{ k}\Omega$			
SIp hold time	tksi1	$4.0 \ V \le EV_{\text{DD0}} \le 5.5 \ V, \ 2.7 \ V \le V_{\text{b}} \le 4.0 \ V,$	38		ns
(from SCKp↑) ^{Note}		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \le EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \le V_{\text{b}} \le 2.7 \ V,$	38		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		$2.4 \ V \leq EV_{\text{DD0}} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$	38		ns
		$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
Delay time from SCKp \downarrow to	tkso1	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$		200	ns
SOp output ^{Note}		$C_b = 30 \text{ pF}, \text{ R}_b = 1.4 \text{ k}\Omega$			
		$2.7 \ V \le EV_{\text{DD0}} < 4.0 \ V, \ 2.3 \ V \le V_{\text{b}} \le 2.7 \ V,$		390	ns
		C_b = 30 pF, R_b = 2.7 k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$		966	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)
 (T₁ = 40 to ±105°C 2.4 V ≤ EVere = EVere ≤ Vere ≤ 5.5 V, Vere = EVere = 6.V)

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)



3.8 Flash Memory Programming Characteristics

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclĸ	$2.4~V \leq V_{DD} \leq 5.5~V$	1		32	MHz
Number of code flash rewrites Notes 1,2,3	Cerwr	Retained for 20 years TA = 85° C ^{Note 4}	1,000			Times
Number of data flash rewrites Notes 1,2,3		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85° C ^{Note 4}	100,000			
		Retained for 20 years TA = 85°C ^{Note 4}	10,000			

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library.
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- 4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

$(T_{\text{A}} = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{ V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



3.10 Timing of Entry to Flash Memory Programming Modes

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.
- **Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
 - t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level
 - thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



4. PACKAGE DRAWINGS

4.1 20-pin Products

R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12



Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

	()
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
Ι	6.1±0.2
J	1.0±0.2
К	0.17±0.03
L	0.5
Μ	0.13
Ν	0.10
Р	3° ^{+5°} 3°
Т	0.25
U	0.6±0.15

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4.4 30-pin Products

R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AGASP R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP R5F100AAGSP, R5F100ACGSP, R5F100ADGSP, R5F100AEGSP, R5F100AFGSP, R5F100AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18





0.5

0.13

0.10 3°+5°

0.25

0.6±0.15

L

M N

P T

U

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R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG, R5F100LJABG

R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG, R5F101LJABG

R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LHGBG, R5F100LJGBG

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-VFBGA64-4x4-0.40	PVBG0064LA-A	P64F1-40-AA2-2	0.03



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R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F100PLDFA R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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0.10

0.575

0.825

y ZD

ZE

Rev.			Description
	Date	Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		109	Addition of (1) I ² C standard mode
		111	Addition of (2) I ² C fast mode
		112	Addition of (3) I ² C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)